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AMENDMENTS TO THE ABSTRACT:

Please cancel the originally filed Abstract and replace it with the new Abstract on the following page.

ABSTRACT OF THE DISCLOSURE

A semiconductor power converting apparatus including at least one series arrangement of MOS control semiconductor devices such as Insulator-gate Bipolar Transistors (IGBTs) or metal oxide MOS transistors which are respectively applied with a gate voltage under the control of corresponding a driver. The driver contains a supply line having a higher potential than a gate voltage of an IGBT coupled thereto when the IGBT is in a steady ON state, and is such that it causes an increase of the gate voltage of the IGBT in accordance with the current of the supply line when a potential difference between the power supply line and an emitter of the IGBT is constant and the collector voltage thereof exceeds a predetermined value under an ON state of the IGBT.